Silicon PNP Darlington Power Transistors 2SB1624

DESCRIPTION

・With TO-3PN package
・Complement to type 2SD2493

APPLICATIONS

・Audio ,regulator and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

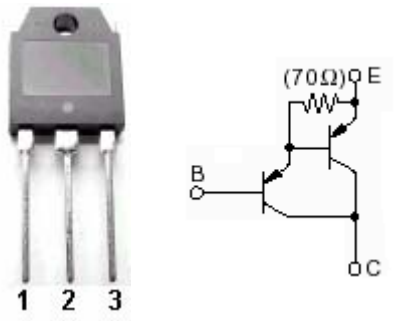

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-110	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-6	A
I_B	Base current		-1	A
P_C	Collector power dissipation	T_C=25℃	60	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-30mA ;I_B=0	-110			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5A ;I_B=-5mA			-2.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-5A ;I_B=-5mA			-3.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-110V; I_E=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-100	μA
h_{FE}	DC current gain	I_C=-5A ; V_{CE}=-4V	5000			
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		110		pF
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-12V		100		MHz
Switching times						
t_{on}	Turn-on time	I_C=-5A;R_L=6Ω I_{B1}=- I_{B2}=-5mA V_{CC}=-30V		1.1		μs
t_s	Storage time			3.2		μs
t_f	Fall time			1.1		μs

◆ h_{FE} Classifications

O	P	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

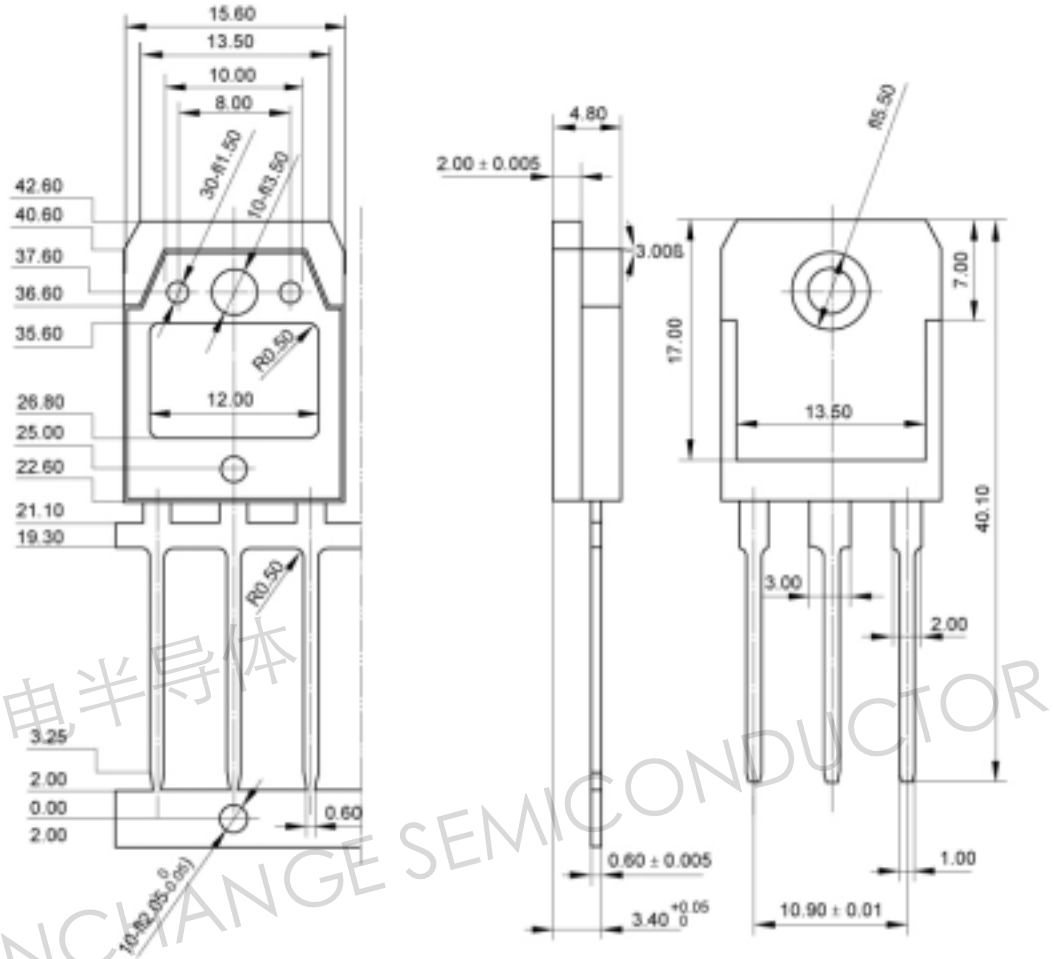

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)